Central
Semiconductor Corp.
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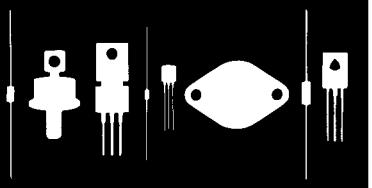
145 Adams Avenue
Hauppauge, New York 11788



1N4151 THRU 1N4154

SILICON SWITCHING DIODE

JEDEC DO-35 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 1N4151 Series types are Hermetically Sealed Silicon Diodes designed for fast switching applications.

MAXIMUM RATINGS (T_A=25°C)

	SYMBOL	1N4151	1N4152	1N4153	1N4154	UNIT
Peak Repetitive Reverse Voltage	V_{RRM}	75	40	75	35	V
Peak Working Reverse Voltage	V_{RWM}	50	30	50	25	V
Average Forward Current	I_O	150	150	150	150	mA
Peak Forward Surge Current	I_{FSM}	1000	1000	1000	1000	mA
Power Dissipation	P_D	500	500	500	500	mW
Operating and Storage Junction Temperature	T_J, T_{stg}		-65 TO +200			°C

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

		1N4151		1N4152		1N4153		1N4154		
SYMBOL	TEST CONDITIONS	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	UNIT
BV_R	I_R=5.0uA	75		40		75		35		V
I_R	V_R=Rated V_{RWM}		0.05		0.05		0.05		0.1	uA
I_R	V_R=Rated V_{RWM}, T_A=150°C		50		50		50		100	uA
V_F	I_F=0.1mA			0.49	0.55	0.49	0.55			V
V_F	I_F=0.25mA			0.53	0.59	0.53	0.59			V
V_F	I_F=1.0mA			0.59	0.67	0.59	0.67			V
V_F	I_F=2.0mA			0.62	0.70	0.62	0.70			V
V_F	I_F=10mA			0.70	0.81	0.70	0.81			V
V_F	I_F=20mA			0.74	0.88	0.74	0.88			V
V_F	I_F=30mA								1.0	V
V_F	I_F=50mA		1.0							V
C_T	V_R=0, f=1.0MHz		2.0		2.0		2.0		4.0	pF
t_{rr}	I_F=10mA, I_{RM}=10mA, i_{rr}=1.0mA, R_L=100Ω		4.0		4.0		4.0		4.0	ns
t_{rr}	I_F=10mA, I_{RM}=6mA, i_{rr}=1.0mA, R_L=100Ω		2.0		2.0		2.0		2.0	ns

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